

Title (en)  
METHOD OF FABRICATING A GATE STACK AT LOW TEMPERATURE

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES MEHRSCHICHT-GATES BEI NIEDRIGER TEMPERATUR

Title (fr)  
PROCEDE D'EMPILEMENT DE GRILLE A BASSE TEMPERATURE

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Application  
**EP 02798410 A 20020826**

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Abstract (en)  
[origin: TW559916B] The present invention relates to methods for forming dielectric layers on a substrate, such as in an integrated circuit. In one aspect of the invention, a thin interfacial layer is formed (30). The interfacial layer is preferably an oxide layer and a high-k material is preferably deposited on the interfacial layer by a process that does not cause substantial further growth of the interfacial layer. For example, water vapor may be used as an oxidant source during high-k deposition at less than or equal to about 300 DEG C.

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